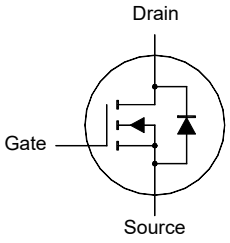
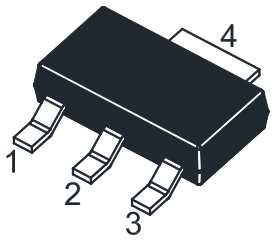
WTQ06N750LS-AH

N-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Low threshold drive
- Halogen and Antimony Free(HAF), RoHS compliant





1.Gate 2.Drain 3.Source 4.Drain
SOT-223 Plastic Package

Applications

- Switching applications
- DC-DC converters for Telecom and Computer

Key Parameters

Parameter	Value	Unit
BV_{DSS}	60	V
$R_{DS(ON)}$ Max	78 @ V_{GS} = 10 V	mΩ
	100 @ V_{GS} = 4.5 V	
$V_{GS(th)}$ typ	1.7	V
Q_g typ	4.3 @ V_{GS} = 4.5 V	nC

Absolute Maximum Ratings (at T_a = 25℃ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current T_c = 25℃ T_c = 100℃	I_D	4 2.9	A
Peak Drain Current, Pulsed [1]	I_{DM}	16	A
Single-Pulse Avalanche Current	I_{AS}	5.4	A
Single-Pulse Avalanche Energy [2]	E_{AS}	1.5	mJ
Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	℃

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	20	℃/W
Thermal Resistance - Junction to Ambient [3] Steady State	$R_{\theta JA}$	100	℃/W

[1] Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 2%, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ = 150°C.

[2] Limited by $T_{J(MAX)}$, starting T_J = 25 °C, L = 0.1 mH, R_g = 25 Ω, I_D = 5.4 A, V_{GS} = 10 V.

[3] Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Dated: 26/03/2021 SGF0 Rev: 02

Characteristics at T_a = 25℃ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at I_D = 250 µA	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current at V_{DS} = 48 V	I_{DSS}	-	-	1	µA
Gate Leakage Current at V_{GS} = ± 20 V	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at V_{DS} = V_{GS}, I_D = 250 µA	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at V_{GS} = 10 V, I_D = 2 A at V_{GS} = 4.5 V, I_D = 1.5 A	$R_{DS(on)}$	- -	68 -	78 100	mΩ
DYNAMIC PARAMETERS					
Gate Resistance at V_{DS} = 0 V, V_{GS} = 0 V, f = 1 MHz	R_g	-	0.9	-	Ω
Forward Transconductance at V_{DS} = 5 V, I_D = 2 A	g_{FS}	-	3.9	-	S
Input Capacitance at V_{DS} = 30 V, V_{GS} = 0 V, f = 1 MHz	C_{iss}	-	446.6	-	pF
Output Capacitance at V_{DS} = 30 V, V_{GS} = 0 V, f = 1 MHz	C_{oss}	-	26	-	pF
Reverse Transfer Capacitance at V_{DS} = 30 V, V_{GS} = 0 V, f = 1 MHz	C_{rss}	-	5	-	pF
Gate Charge Total at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A at V_{DS} = 30 V, V_{GS} = 4.5 V, I_D = 3 A	Q_g	- -	8.1 4.3	- -	nC
Gate to Source Charge at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A	Q_{gs}	-	1.9	-	nC
Gate to Drain Charge at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A	Q_{gd}	-	1.9	-	nC
Turn-On Delay Time at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A, R_g = 4.7 Ω	$t_{d(on)}$	-	7	-	ns
Turn-On Rise Time at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A, R_g = 4.7 Ω	t_r	-	3	-	ns
Turn-Off Delay Time at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A, R_g = 4.7 Ω	$t_{d(off)}$	-	6	-	ns
Turn-Off Fall Time at V_{DS} = 30 V, V_{GS} = 10 V, I_D = 3 A, R_g = 4.7 Ω	t_f	-	2	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at I_S = 4 A, V_{GS} = 0 V	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_S	-	-	4	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	16	A
Body Diode Reverse Recovery Time at I_S = 4 A, di/dt = 100 A / µs	t_{rr}	-	8.4	-	ns
Body Diode Reverse Recovery Charge at I_S = 4 A, di/dt = 100 A / µs	Q_{rr}	-	4.6	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristic

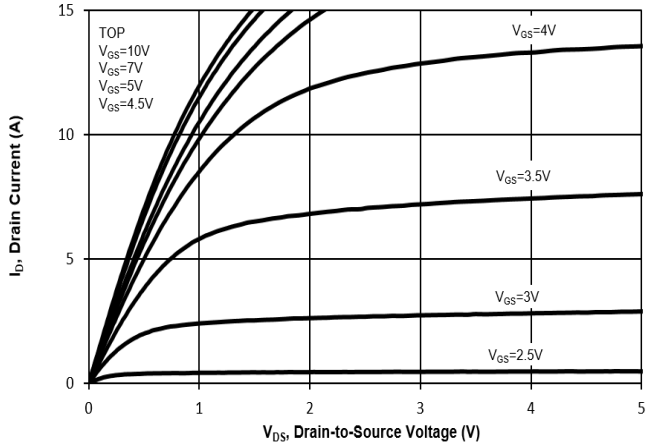


Fig. 2 Typical Transfer Characteristic

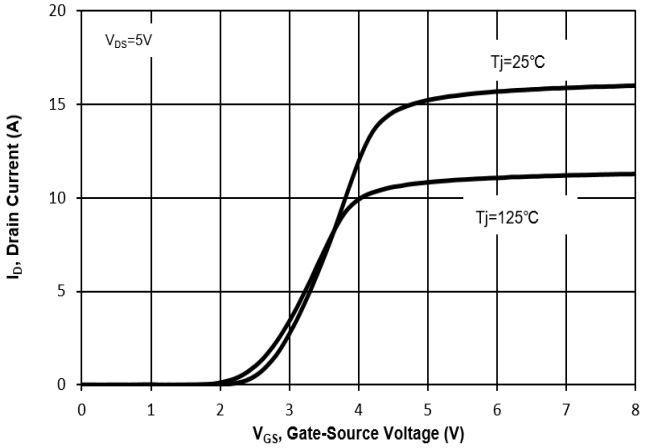


Fig. 3 On-Resistance vs. Drain Current

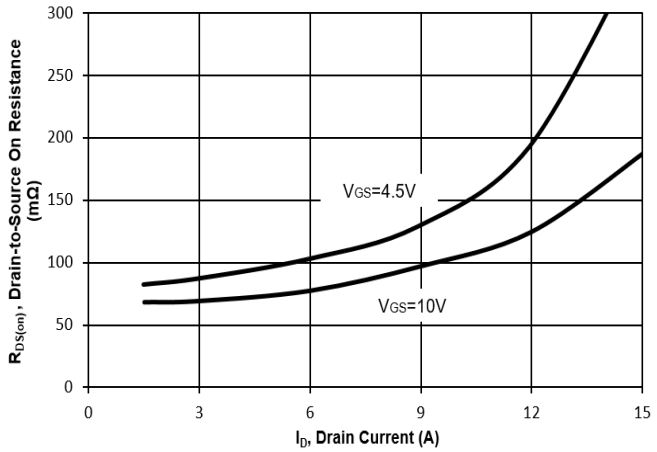


Fig. 4 On-Resistance vs. Gate Voltage

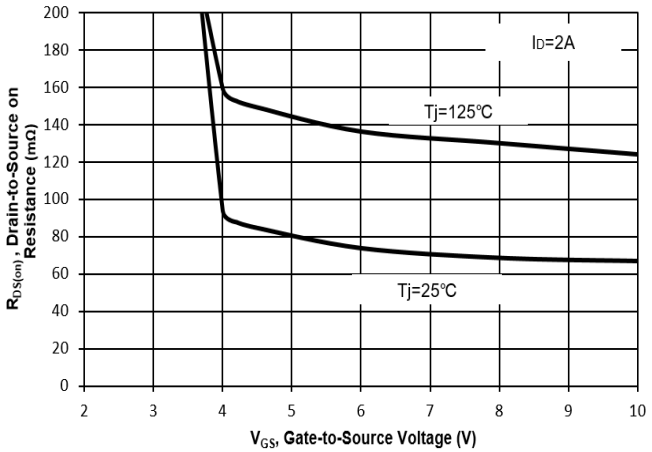


Fig. 5 On-Resistance vs.T_j

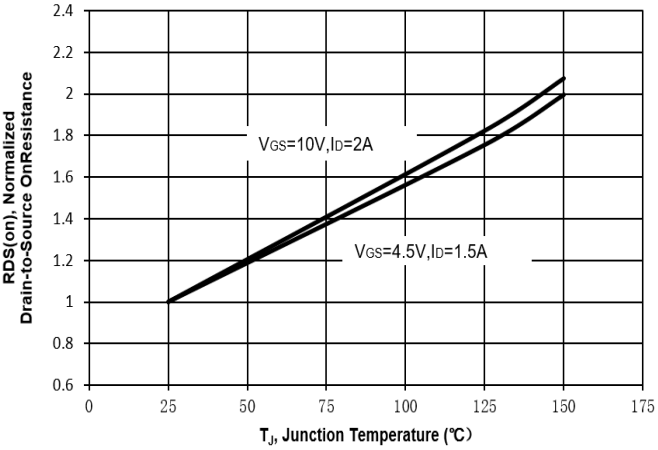
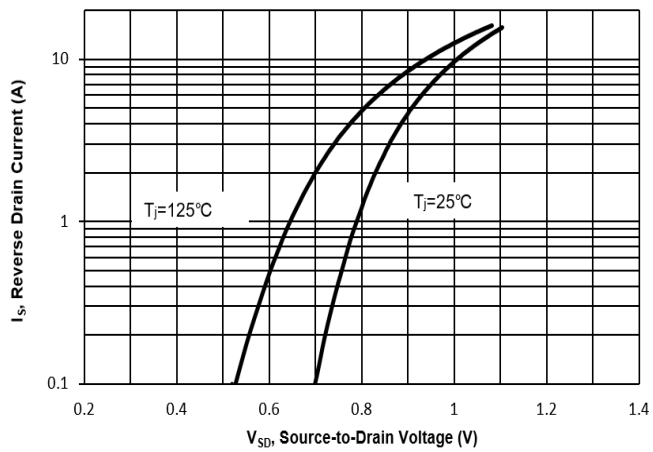


Fig. 6 Typical Body-Diode Forward Characteristic



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

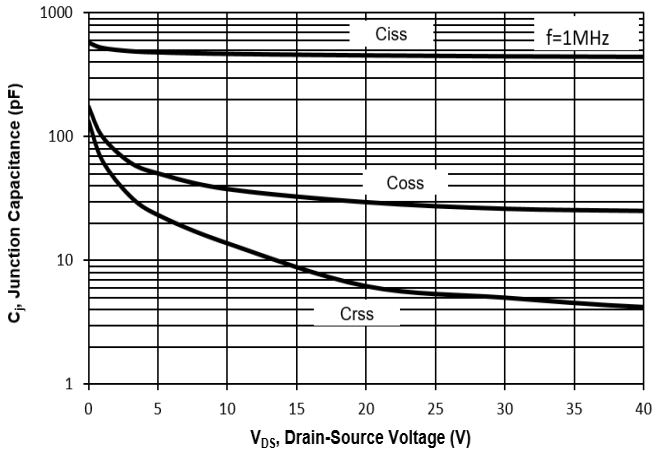


Fig. 8 Drain-Source Leakage Current vs. T_j

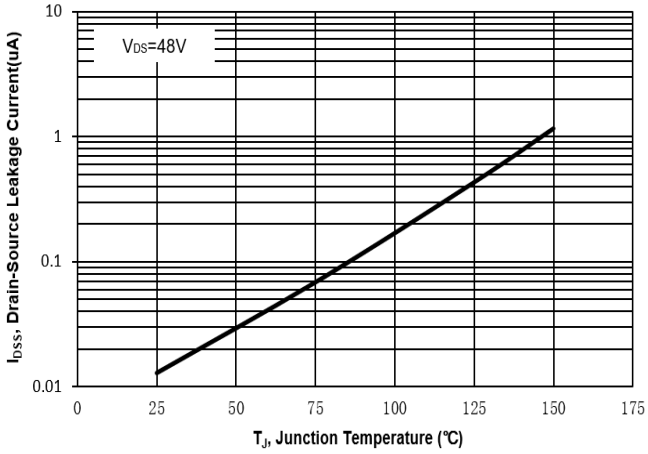


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

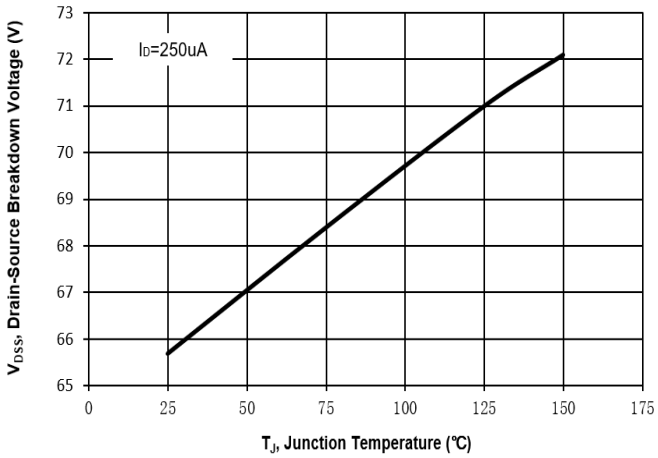


Fig. 10 Gate Threshold Variation vs. T_j

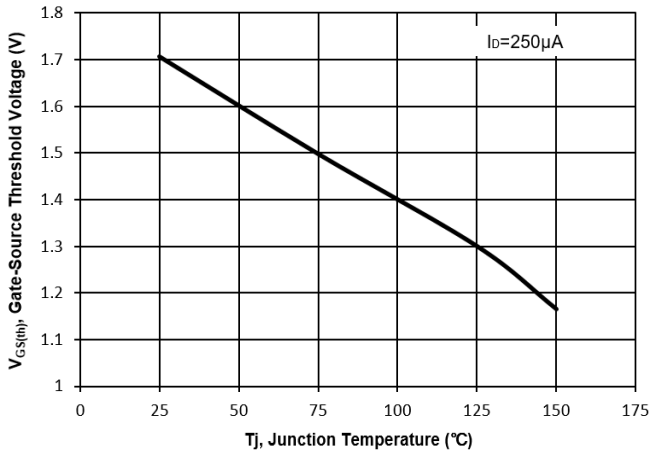


Fig. 11 Gate Charge

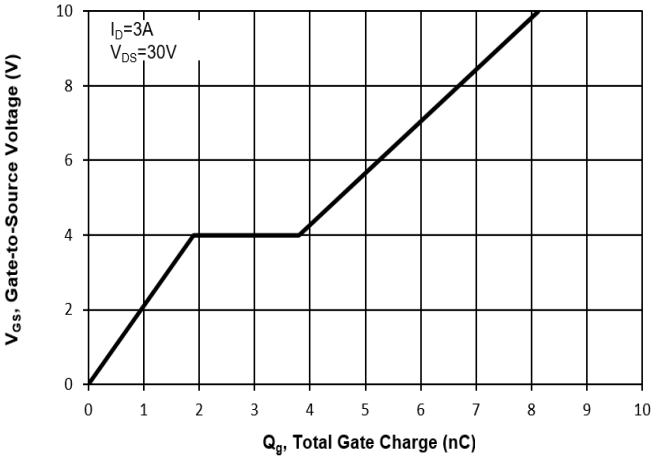
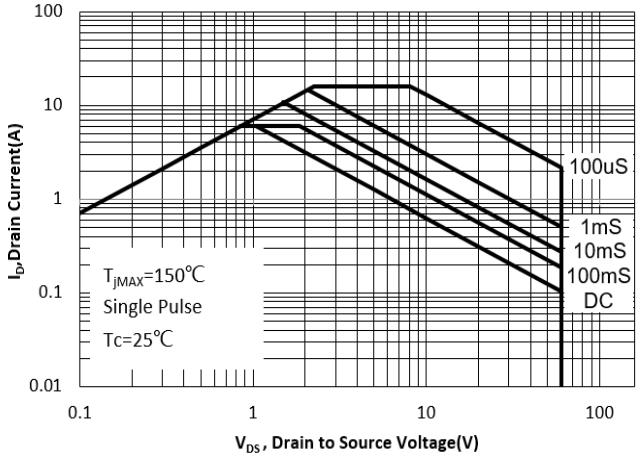
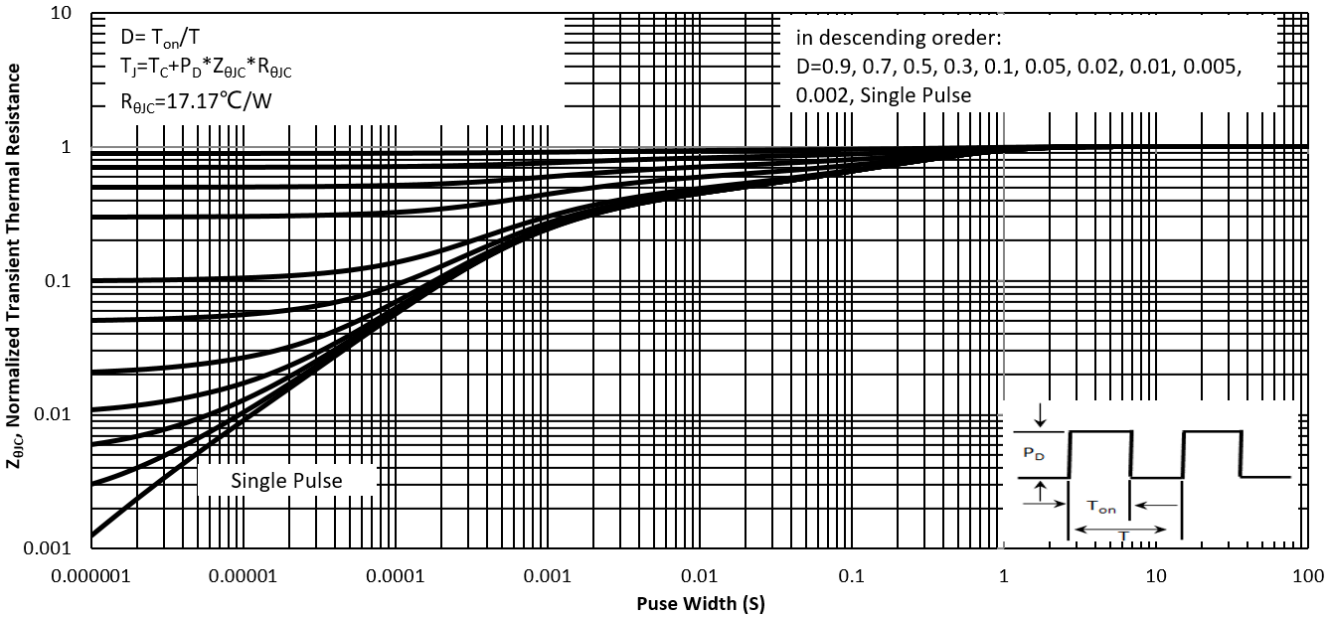


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig.13 Normalized Maximum Transient Thermal Impedance($z_{\Theta JC}$)



Test Circuits

Fig.1-1 Switching times test circuit

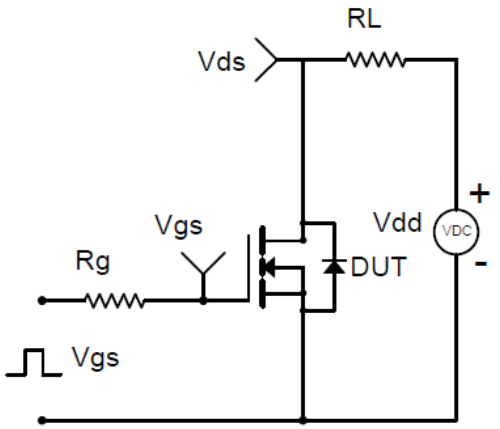


Fig.1-2 Switching Waveform

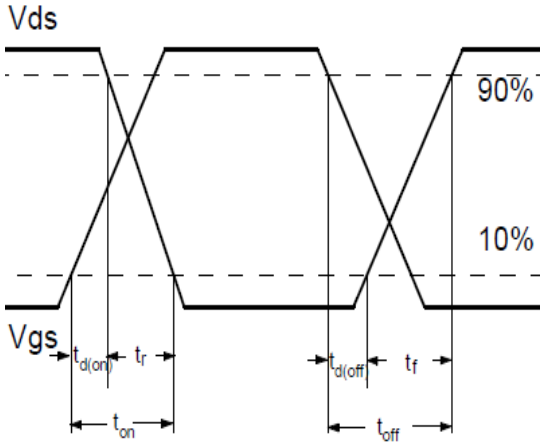


Fig.2-1 Gate charge test circuit

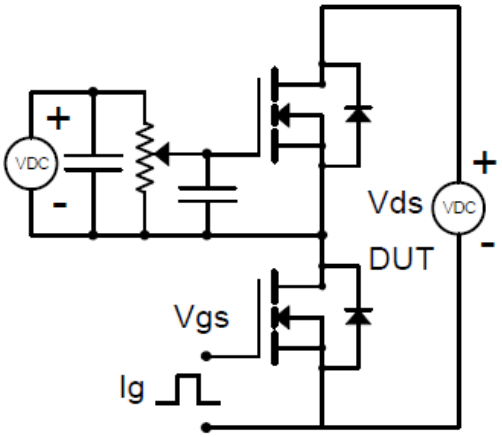


Fig.2-2 Gate charge waveform

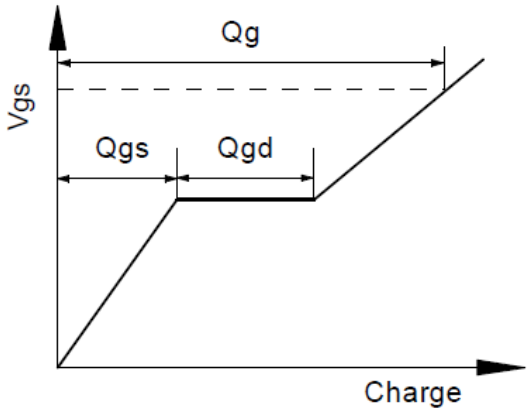


Fig.3-1 Avalanche test circuit

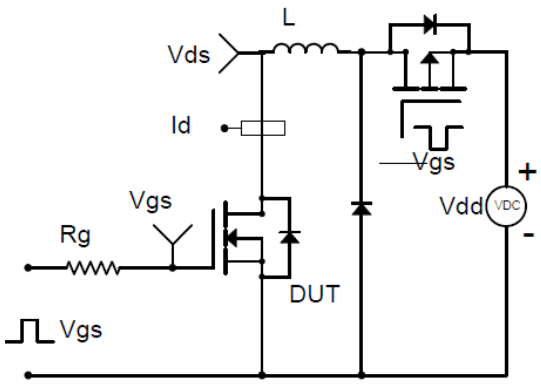
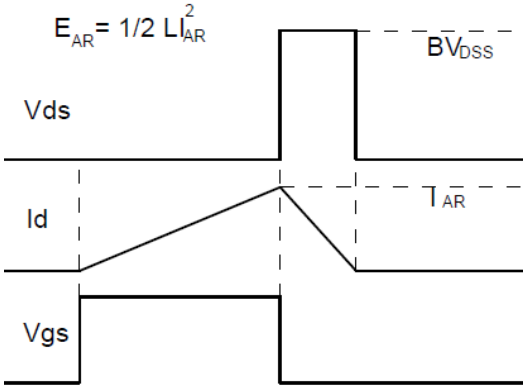
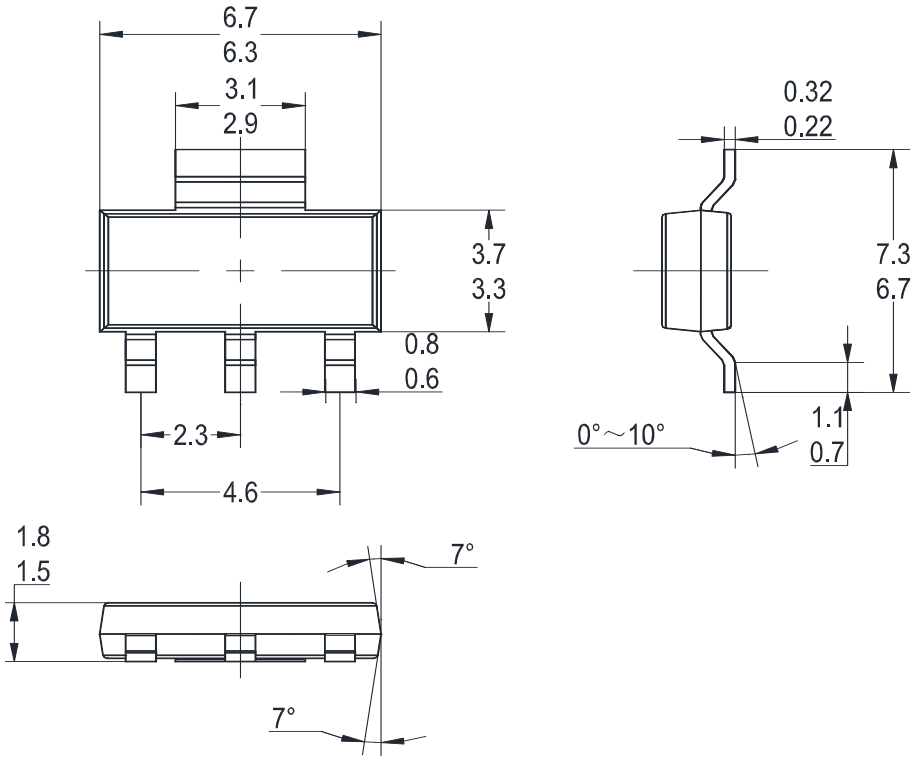


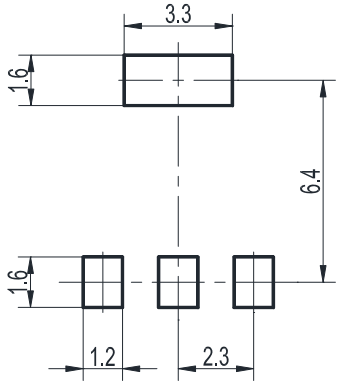
Fig.3-2 Avalanche waveform



Package Outline (Dimensions in mm) SOT-223



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" TQ06N750LS " = Part No.

" ****** " = Date Code Marking

Font type: Arial

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